



IRLR110PBF Information



For Reference Only

Part Number IRLR110PBF
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 4.3A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63 For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRLR110PBF Specifications

Manufacturer Part Number IRLR110PBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 4.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C4.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 4.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Curent - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs 6.1nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C4.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C4.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +10V FET Feature - Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Found Temperature Supplier Device Package Package / Case 2V @ 250μA 6.1nC @ 5V 250pF @ 25V 25	Current - Continuous Drain (Id) @ 25°C	4.3A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4V, 5V
Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) $\pm 10 \text{V}$ FET Feature-Power Dissipation (Max) 2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A , 5V Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C}$ (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	6.1nC @ 5V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	250pF @ 25V
Power Dissipation (Max) 2.5W (Ta), 25W (Tc) 8ds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	2.5W (Ta), 25W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	540 mOhm @ 2.6A, 5V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IRLR110PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLR110PBF Payment Methods



















IRLR110PBF Shipping Methods













If you have any question about IRLR110PBF, please do not hesitate to contact us!

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